

## ABSTRACT OF THE DISCLOSURE

A process for cleaning an integrated circuit package surface, comprising the steps of introducing the integrated circuit inside a plasma chamber; and of exposing the integrated circuit to a physical plasma obtained starting from a gas consisting of pure argon or any other noble gas having, in the plasma state, the behavior of a halogen, for example helium. The argon plasma is obtained using the following energization parameters: energization time, 12-13 seconds; energization power, 140-160 W; plasma chamber pressure, 190-210 millitorr; and energization frequency, between 1 kHz and 100 GHz.

854063 654 / 19346 1 Doc

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